

Si PIN photodiodes



S3096-02

S4204

Dual-element, plastic package photodiode

The S3096-02 and S4204 are dual-element Si PIN photodiodes molded into plastic packages. Having high sensitivity and low noise, these photodiodes have low crosstalk between the elements. Custom devices (with different element shapes, number of elements, characteristics and packages) are also available to meet your specific needs. Please feel free to contact our sales office.

Features

- High sensitivity
- Uniform element sensitivity
- Low crosstalk
- Low noise

Applications

- Optical switch
- Various position detection applications

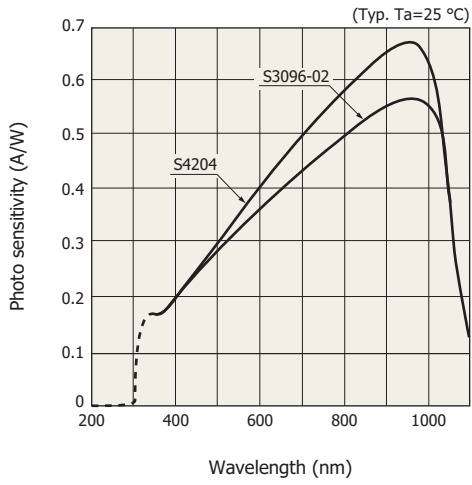
General ratings / Absolute maximum ratings

Parameter	Symbol	S3096-02	S4204	Unit
Active area	-	1.2 × 3 / 2 elements	1 × 2 / 2 elements	mm
Element gap	-	30	20	μm
Reverse voltage	V _R Max.	20		V
Operating temperature	T _{opr}	-25 to +85		°C
Storage temperature	T _{stg}	-40 to +100		°C

Electrical and optical characteristics (Typ. T_a=25 °C, unless otherwise noted, per 1 element)

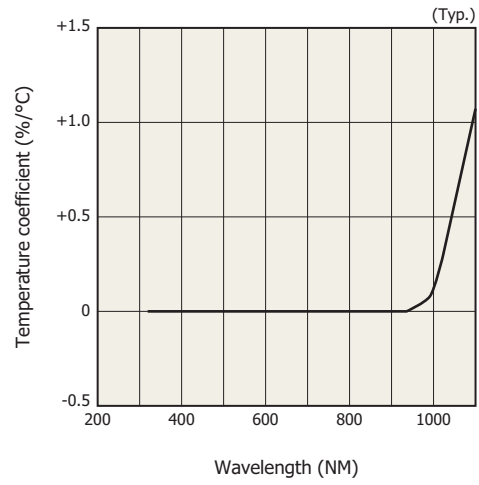
Parameter	Symbol	Condition	S3096-02			S4204			Unit
			Min.	Typ.	Max.	Min.	Typ.	Max.	
Spectral response range	λ		-	320 to 1100	-	-	320 to 1100	-	nm
Peak sensitivity wavelength	λ _p		-	960	-	-	960	-	nm
Photo sensitivity	S	λ=λ _p	-	0.58	-	-	0.65	-	A/W
Dark current	I _D	V _R =10 V, all elements	-	0.05	0.5	-	0.1	1.0	nA
Temp. coefficient of I _D	T _{CI_D}		-	1.15	-	-	1.15	-	times/°C
Cut-off frequency	f _c	V _R =10 V, R _L =50 Ω λ=780 nm, -3 dB	-	25	-	-	30	-	MHz
Terminal capacitance	C _t	V _R =10 V, f=1 MHz	-	5	-	-	3	-	pF
Noise equivalent power	NEP	V _R =10 V	-	7.2 × 10 ⁻¹⁵	-	-	8.7 × 10 ⁻¹⁵	-	W/Hz ^{1/2}

Spectral response



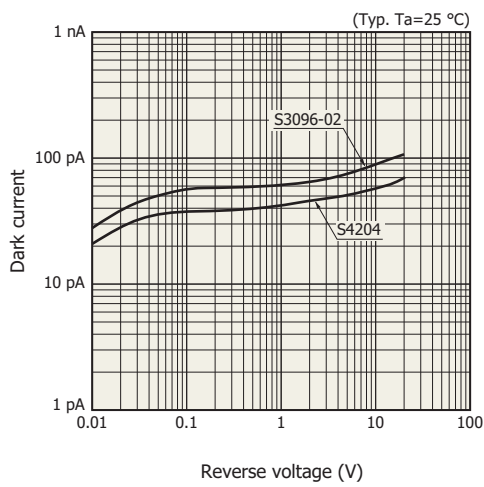
KMPD80134EC

Photo sensitivity temperature characteristic



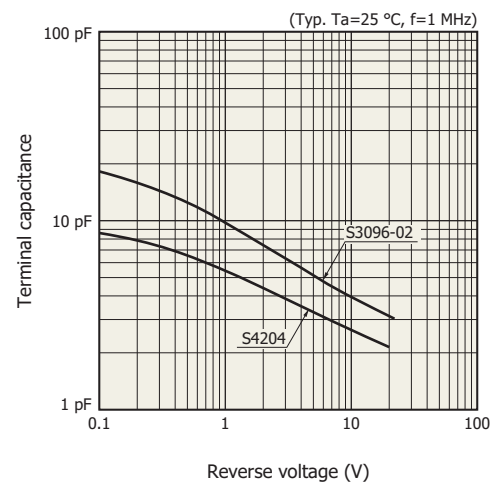
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Dark current vs. reverse voltage



KMPD80136EC

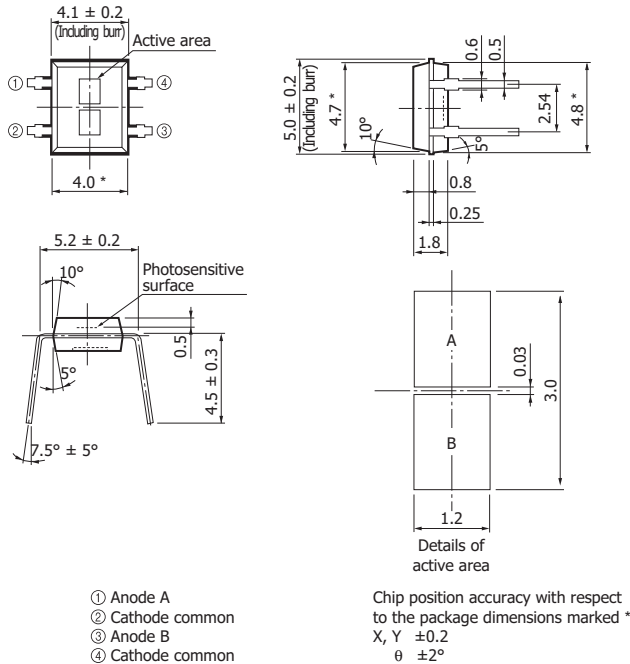
Terminal capacitance vs. reverse voltage



KMPD80137EC

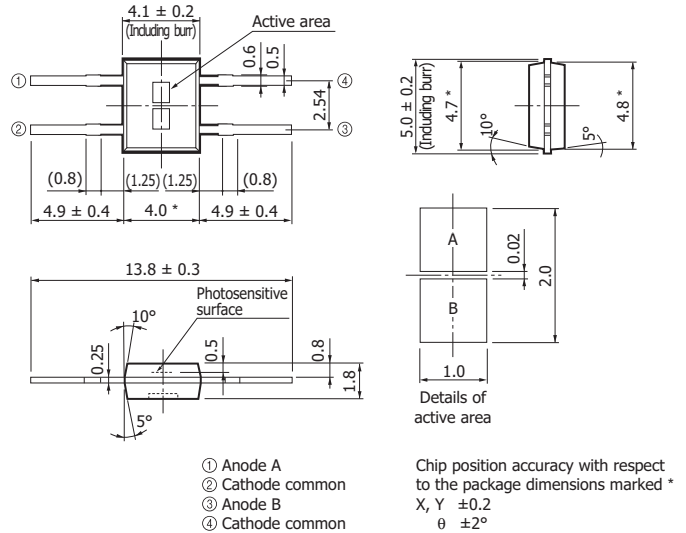
Dimensional outlines (unit: mm, tolerance unless otherwise noted: ± 0.1)

S3096-02



KMPDA0119EB

S4204



KMPDA0120EB

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HAMAMATSU PHOTONICS K.K., Solid State Division

1126-1 Ichino-cho, Higashi-ku, Hamamatsu City, 435-8558 Japan, Telephone: (81) 53-434-3311, Fax: (81) 53-434-5184

U.S.A.: Hamamatsu Corporation: 360 Foothill Road, P.O.Box 6910, Bridgewater, N.J. 08807-0910, U.S.A., Telephone: (1) 908-231-0960, Fax: (1) 908-231-1218

Germany: Hamamatsu Photonics Deutschland GmbH: Arzbergerstr. 10, D-82211 Herrsching am Ammersee, Germany, Telephone: (49) 08152-3750, Fax: (49) 08152-2658

France: Hamamatsu Photonics France S.A.R.L.: 19, Rue du Saule Trapu, Parc du Moulin de Massy, 91882 Massy Cedex, France, Telephone: 33-(1) 69 53 71 00, Fax: 33-(1) 69 53 71 10

United Kingdom: Hamamatsu Photonics UK Limited: 2 Howard Court, 10 Tewin Road, Welwyn Garden City, Hertfordshire AL7 1BW, United Kingdom, Telephone: (44) 1707-294888, Fax: (44) 1707-325777

North Europe: Hamamatsu Photonics Norden AB: Smidesvägen 12, SE-171 41 Solna, Sweden, Telephone: (46) 8-509-031-00, Fax: (46) 8-509-031-01

Italy: Hamamatsu Photonics Italia S.R.L.: Strada della Moia, 1/E, 20020 Arese, (Milano), Italy, Telephone: (39) 02-935-81-733, Fax: (39) 02-935-81-741